

NPN Power Silicon Transistor



Rev. V4

Features

- Available in JAN, JANTX, JANTXV per MIL-PRF-19500/526
- TO-66 (TO-213AA) Package
- Ideal for High Speed Switching and Linear Amplifier Applications



Electrical Characteristics (T_A = +25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Units	Min.	Max.	
	r r	1				
Collector - Emitter Breakdown Voltage	I _C = 200 mA dc	V _{(BR)CEO}	V dc	75	_	
Collector - Emitter Cutoff Current	V _{CE} = 50 V dc	I _{CEO}	mA dc	—	5	
Collector - Emitter Cutoff Current	V _{CE} = 100 Vdc, V _{BE} = 1.5 V dc	I _{CEX1}	µA dc	_	10	
Collector - Base Cutoff Current	V _{CB} = 120 V dc	I _{CBO}	µA dc	_	10	
Emitter - Base Cutoff Current	V _{EB} = 7 V dc	I _{EBO}	mA dc	—	10	
Forward Current Transfer Ratio	$ I_{C} = 0.5 \text{ A dc}, V_{CE} = 5 \text{ V dc} I_{C} = 4.0 \text{ A dc}, V_{CE} = 5 \text{ V dc} I_{C} = 4.0 \text{ A dc}, V_{CE} = 2 \text{ V dc} $	h _{FE}	-	30 20 12	— 80 100	
Collector - Emitter Saturation Voltage	$I_{\rm C}$ = 4.0 A dc, $I_{\rm B}$ = 0.4 A dc	$V_{\text{CE}(\text{SAT})}$	V dc	—	1.2	
Base - Emitter Saturation Voltage	$I_{\rm C}$ = 4.0 A dc, $I_{\rm B}$ = 0.4 A dc	$V_{\text{BE}(\text{SAT})}$	V dc	—	2.0	
Base - Emitter Voltage	$I_{\rm C}$ = 4.0 A dc, $I_{\rm B}$ = 2.0 A dc	V_{BE}	V dc	_	1.8	
Dynamic Characteristics						
Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio	$I_{\rm C}$ = 500 mA dc, $V_{\rm CE}$ = 10 Vdc, f = 10 mHz	h _{fe}	-	4	20	
Output Capacitance	V_{CB} = 10 Vdc, I _E = 0, 0.1 MHz ≤ f ≤ 1 MHz	C _{obo}	pF	_	175	
Switching Characteristics						
Turn-On Time	$V_{CC} = 30 V dc; I_{C} = 4.0 A dc;$ $I_{B} = 0.4 A dc$	t _{on}	μs	_	0.25	
Turn-Off Time	V_{CC} = 30 Vdc; I _C = 4.0 A dc; I _B = -I _B = 0.4 A dc	t _{off}	μs	_	2.5	

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Parameter	Test Conditions	Symbol	Units	Min.	Max.
Collector - Emitter Cutoff Current	$T_A = +150^{\circ}C$ V _{CE} = 100 Vdc; V _{BE} = 1.5 V dc	I _{CEX2}	µA dc	_	750
Forward - Current Transfer Ratio	V _{CE} = 5.0 V dc; I _C = 0.5 A dc	h _{FE4}		10	

Absolute Maximum Ratings ($T_A = + 25^{\circ}C$ unless otherwise noted)

Ratings	Symbol	Value
Collector - Emitter Voltage	V_{CEO}	75 V dc
Collector - Base Voltage	V _{CBO}	120 V dc
Emitter - Base Voltage	V_{EBO}	7 V dc
Base Current	I _B	5 V dc
Collector Current	Ι _C	7 A dc
Total Power Dissipation @ $T_c = 25^{\circ}C^1$	P _T	35 W
Operating & Storage Temperature Range	T _J , T _{STG}	-65°C to +200°C

1. Derate linearly @ 200 mW /°C for $T_C > 25^{\circ}C$.

Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Case	$R_{\theta JC}$	5°C/W

Safe Operating A	Area	
DC Tests: Test 1: Test 2: Test 3: Test 4:	T_{C} = +25 °C, I Cycle, t = 1.0 s V_{CE} = 5 Vdc, I _C = 7 Adc V_{CE} = 28 Vdc, I _C = 1.25 Adc V_{CE} = 40 Vdc, I _C = 500 Adc V_{CE} = 75 Vdc, I _C = 100 Adc	

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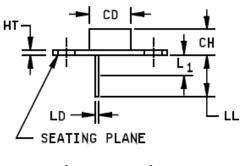
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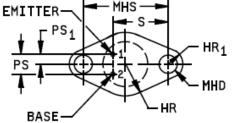


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Outline Drawing (TO-66)

	Dimensions					
Symbol	Inches		Millimeters		Notes	
	Min	Max	Min	Мах		
CD	.470	.500	11.94	12.70	3,10	
СН	.250	.340	6.35	8.64		
HR		.350		8.89		
HT	.050	.075	1.27	1.91		
HR ₁	.115	.145	2.92	3.68	8	
LD	.028	.034	0.71	0.86	3,7,10	
LL	.360	.500	9.14	12.70	3,9	
L ₁		.050		1.27	9	
MHD	.142	.152	3.61	3.86	7,10	
MHS	.958	.962	24.33	24.43		
PS	.190	.210	4.83	5.33	4	
PS ₁	.093	.107	2.36	2.72	4	
s	.570	.590	14.48	14.99		





NOTES:

- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. Body contour is optional within zone defined by CD and PS1.
- These dimensions should be measured at points .050 inch (1.27 mm) .055 inch (1.40 mm) below seating plane. When gauge is not used measurement will be made at the seating plane.
- 5. Both terminals.
- At both ends.
- Two holes.
- 8. The collector is electrically connected to the case.
- 9. LD applies between L1 and LL. Lead diameter shall not exceed twice LD within L1.
- 10. In accordance with ASME Y14.5M, diameters are equivalent to \$\phi x\$ symbology.

FIGURE 1. Physical dimensions (TO-66).

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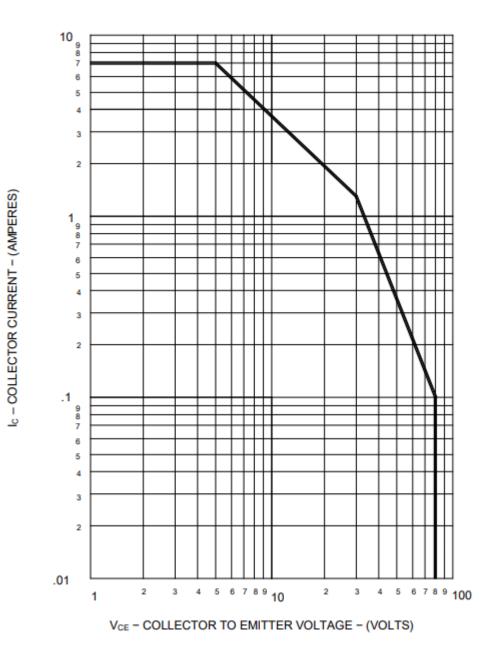
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Maximum Safe Operating Graph





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Maximum Safe Operating Graph

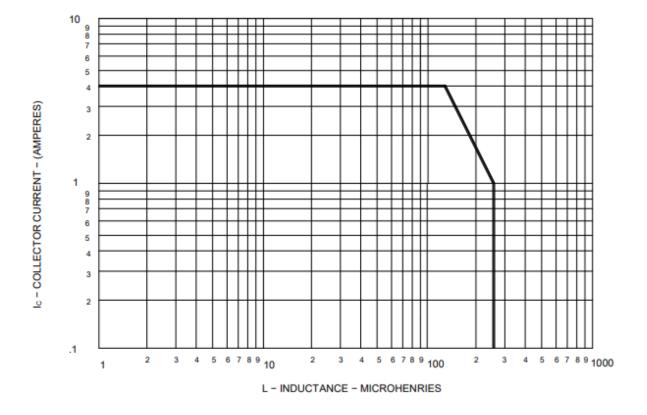


FIGURE 4. Safe operating area for switching between saturation and cutoff (unclamped load).

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